P robing the phase diagram of $C \in R u_2 G \in Q$ by therm opower at high pressure

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The tem perature dependence of the therm oelectric power, S (T), and the electrical resistivity of the magnetically ordered C eR $u_2 G e_2 \ (T_N = 8.55 \ K$ and $T_C = 7.40 \ K$) were measured for pressures $p < 16 \ GPa$ in the tem perature range $1.2 \ K < T < 300 \ K$. Long-range magnetic order is suppressed at $p_c = 6.4 \ GPa$. Pressure drives S (T) through a sequence of tem perature dependences, ranging from a behaviour characteristic for magnetically ordered heavy ferm ion compounds to a typical behaviour of interm ediate-valent system s. At interm ediate pressures a large positive maximum develops above 10 K in S (T). Its origin is attributed to the K ondo e ect and its position is assumed to re ect the K ondo tem perature T_K . The pressure dependence of T_K is discussed in a revised and extended (T;p) phase diagram of C eR $u_2 G e_2$.

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I. IN TRODUCTION

A large num ber of heavy ferm ion (HF) or unstable valence com pounds and alloys revealed a com plicated tem perature (T) dependence of the therm oelectric power (S). This is due to competing interactions present in these system s and the sensitivity of S to details of the band structure. Depending on the strength of the hybridisation between 4f and conduction electrons, the exchange interaction J leads to long-range m agnetic order, m agnetic Kondo systems, HF or intermediate-valence (IV) behaviour. As a measure for the strength of J of these four regimes one can use the K ondo temperature T_{K} and the N celtern perature T_N (or the C urie tem perature T_C). Sakurai and coworkers [1] used the ratio of T_K to T_N to classify the S(T) data of di erent compounds into these regimes, each showing a characteristic S (T) dependence. Ce-based representatives of each regime investigated by S (T) are CeA u₂ Siz [2], CeA 上 [3], CeA 上 [4] and CeRu₂Si₂ [5,6] or CeN i₂Si₂ [7,8].

Typical features in S (T) of these regimes can be seen in a single compound if J is increased, e.g. by alloying. Increasing x in the pseudo-binary alloy $Ce(Pb_1 \ _x Sn_x)_3$ [9] and in the solid-solution $CeRh_2 \ _xNi_xSi_2$ [7] tunes the system s from trivalent to interm ediate-valent, i.e. enhancing J. A lso the interatom ic distances seem to control the shape of S (T). This results from an analysis of the S (T) data of m any $CeM \ _2X \ _2$ compounds, with M a transition m etal and X = Si or Ge [10]. Apparently, in the series $CeM \ _2Si_2$, where the corrected interatom ic distances decrease for M = Au, Cu, Rh, Ru, and Fe, the increase of J is accompanied with a characteristic variation of S (T) at low temperatures.

This system atic volum e dependence suggests that S(T) is very sensitive to pressure. Based on the pressure-induced changes in S(T), Link et al. [11] sketched a sequence of S(T) dependences that shows the evolution of

characteristic features in S (T) with pressure. The S (T) of a magnetically ordered system, like $C \in U_2 G \in S$ shows one negative and one positive peak below 20 K and above about 100 K, respectively [10]. In general, pressure will suppress the negative peak and leads to the appearance of new features at low tem peratures. As pressure has tuned the system into the IV regime, only one maximum well above room temperature remains, like in CeNi2Si2 at am bient pressure [8]. Sim ilarly, the application of pressure on the non-magnetic HF compounds CeCu₂Si₂ (T_K 20 K) [12] and CeA \lg (T_K 5K) [13] reduces the m agnitude of the negative peak and leads to the developm ent of two additional positive peaks around 20 K and even lower tem perature. The analysis of these pressure-induced S (T) dependences has led to the conjecture that the pressure-induced maximum in S (T) located at approxim ately 20 K is related to the K ondo e ect [1]. The origin of the high-tem perature maximum, present already at low pressure, is due to the crystal- eld separation of the C e 4f electron energy level from the ground state [14]. Zlatic and coworkers [5] achieved a qualitative understanding of the experim ental results, using the Cogblin-Schrie erm odel and assuming a splitting of the 4f states in the presence of a crystalline electric eld.

The magnetically ordered CeRu₂Ge₂ o ers the possibility to map the pressure dependence of the characteristic features in S (T) since its pressure-induced transition into the HF regime was intensively studied [16, 17, 18, 19, 20, 21]. The ambient pressure S (T) curve [17] contains no maximum below room temperature, which is a consequence of the large energy separation of the crystal- eld levels ($_1 = 500$ K and $_2 = 750$ K [22,23]). A ssum ing that the crystal eld levels are not strongly in uenced by pressure, two distinct positive peaks at low and high temperature in S (T) at intermediate pressures are expected. This could provide insight into the pressure dependence of T_K. M oreover, the S (T) data m ight reveal inform ation about the pressure-

induced change from a magnetically ordered compound (at p = 0) to a HF K ondo-lattice compound (at high pressure), equivalent to $C \in Ru_2Si_2$ ($T_K = 24 \text{ K}$ [24]) at ambient pressure.

II. EXPERIMENTAL DETAILS

The CeRu₂Ge₂ and LaRu₂Ge₂ sam ples have been prepared by arc-melting stoichiom etric am ounts of Ce, La, Ru, and Ge under argon atmosphere. The purity of the elements was 99.99%, except for Ge, which had a purity of 99.999%. X-ray di raction pattern could be indexed according to the ThC r_2 Si₂ structure (I4=m m m) with lattice parameters a = 4.2685(4) A and c = 10.048(3) A for CeRu₂Ge₂ and a = 4.314(2) A and c = 10.129(6) A for LaRu₂Ge₂. Sam ples of the CeRu₂Ge₂ ingot have been used in earlier electrical resistivity, (T) [6, 17], and speci c heat [8] pressure studies.

A clamped Bridgm an anvil cell with synthetic diam onds was used to measure S (T) and (T) in the tem perature range 12 K < T < 300 K. The pressure chamberwasm ade of a non-metallic gasket (pyrophyllite, int = 1 mm) and two steatite disks served as pressure transmitting medium. Electrical leads were attached to the sample (cross-section of 14 108 m²) in such a way that a four-point (T) and, in a separate run, a S (T) measurement could be performed (Fig. 1). The pressure dependence of the superconducting transition temperature of Pb yielded the pressure [25].

A heater (C hrom el w ire), located close to the sm all edge of the sam ple, produced a tem perature gradient T along the sam ple. The opposite edge of the sam – ple rem ained at T₀, the tem perature of the pressure cell [26], and served as reference for the two therm occuples <u>Au</u>Fe (w ith 0.07 at% Fe) and C hrom el. The two m easured therm ovoltages were $V_{AuFe} = (S_{AuFe} S)$ T and $V_{C hrom el} = (S_{C hrom el} S)$ T. The absolute therm oelectric power of the sam ple, S, at T₀ + T=2 is given by:

$$S = S_{\underline{A}\underline{u}Fe} + \frac{S_{C\,h\,rom\,el} S_{\underline{A}\underline{u}Fe}}{1 V_{C\,h\,rom\,el} = V_{A\,uFe}} :$$
(1)

The absolute them opower of <u>Au</u>Fe and Chrom el are assumed to be pressure independent. This seems to be a good assumption since the absolute value of S_{AuFe} at 12 GPa and 4.2 K is only 20% smaller than at ambient pressure [27]. However, small pressure-induced changes in S (T) of the sample should be interpreted carefully.

III. RESULTS

Figure 2 shows the magnetic part, $m_{ag}(T)$, of (T) of CeRu₂Ge₂ at several pressures. It was obtained by subtracting a phonon contribution, approximated as $_{ph}(T) = 0.12$ cm/K T, from the raw data shown in the inset to Fig.2. The slope @ (T)=@T = 0.12 cm/K

FIG.1: Top view of the inner part of the pressure chamber before cosing. C box to the heater two therm occupies (AuFe

Heater

AuFe

FIG.1: Top view of the inner part of the pressure chamber before closing. C lose to the heater two therm occuples (<u>Au</u>Fe and Chrom el) are located on top of the sam ple. The Au-w ire connected at the opposite edge of the sam ple is chosen as reference point for the two therm ovoltage $V_{\underline{A}uFe}$ and $V_{Chrom el}$. Lead is used as pressure gauge. Au-w ires establish the connection through the pyrophyllite gasket. Steatite serves as pressure transm itting m edium.

was deduced from our (T) measurement of the nonmagnetic reference compound $LaRu_2Ge_2$ at ambient pressure for T > 70 K. This approximation had to be used since the measured value of (T) of ${\rm LaR}\,u_2{\rm G}\,e_2$ is slightly overestim ated, presum ably due to m icrocracks. At low temperature m_{ag} (T) is dominated by the magnetic phase transitions, manifested by several discontinuities in m_{aq} (T). The transition temperatures were de ned by the intersection of two tangents drawn to the (T) curve below and above the kink. A hightem perature peak below room tem perature evolves for pressures in the range 7:0 р 10:4 GPa. It is due to the interplay of the Kondo and crystal- eld effects. At interm ediate tem peratures and pressures (e.g. at about 20 K and 5.7 GPa in inset to Fig. 2), incoherent Kondo scattering is clearly increasing. In contrast to other compounds like $C eP d_2 G e_2$ [27], $C eC u_2 G e_2$ [28], and CeCu₅Au [29] its contribution cannot be deconvoluted due to its m odest m agnitude.

The interpretation of the high-tem perature maximum in mag (T) as a result of K ondo exchange interaction between the conduction electrons and the crystal- eld split ground state of the C e³⁺ -ions is supported by the evolution of the positive peak in S (T) below 300 K for p > 3:4 GPa (see Figs. 3 and 4). Its position T_S corresponds to a fraction of the crystal- eld splitting as in many other C e-based compounds and alloys. In C eRu₂G e₂, T_S rst decreases linearly with pressure (-23 K/GPa), attains a minimum around 200 K at about 9 GPa, and then starts to increase. Based on this T_S (p) variation a maximum in S (T) is expected to occur at



FIG.2: M agnetic contribution $_{m \ ag}(T)$ to the electrical resistivity of C eR u_2 G e_2 at di erent pressures. Two di erent antiferrom agnetic phases occur below T_N and T_L . A ferrom agnetic ground state is present below T_C and low pressure. No traces of magnetic order are observed for p > 7 G Pa above 1.2 K. Inset: Raw data of (T) in a linear plot. Incoherent K ondo scattering is apparent for p = 5.7 G Pa.

about 384 K at am bient pressure, well above the lim it of our set-up. The am plitude of the peak grows linearly with pressure (6.4 V/(K GPa)) and attains a maximum value of 55 V/K at about 10 GPa (Fig. 4).

The complicated S (T) below 10 K (inset to Fig. 3) is very likely caused by the onset of magnetic order and to the opening of a spin gap (= 14 K [17, 30]). Pressureinduced changes of the Ferm i surface due to the periodicity of the magnetic ordering (magnetic super-zone e ects) might be the explanation for the di erent lowtem perature S(T) dependences for p < 3:4 GPa. At 5.7 GPa, S(T) is positive over the entire temperature range and a K ondo m axim um at about $T_{K} = 12 \text{ K}$ (in coherent scattering on the ground state) occurred (Fig. 3). The position of the maximum has shifted considerably towards higher tem peratures in S (T) recorded at 7.0 GPa, supporting its assignment to the Kondo e ect. A trace of this maximum can even be anticipated around 40 K at 8.0 GPa as a weak shoulder at the high-tem perature maximum entered at T_{S} 200 K (Fig. 4). Atsu ciently high pressure both peaks m erge. Then the K ondo m ax-



FIG.3: Tem perature dependence of the therm celectric power S (T) of C eRu₂G e₂ at selected pressures. The entrance into the magnetically ordered states is indicated by $T_{\rm N}$, $T_{\rm C}$, and $T_{\rm L}$, as deduced from the (T) data. $T_{\rm K}$ and $T_{\rm S}$ label the centre of broad, pressure-induced maxim a. The inset shows the low-tem perature part of S (T) at low pressure.

in um dom inates the high-tem perature maximum as the crystal- eld e ect disappears when the system enters the IV regime. At 15.6 GPa, the S (T) maximum is well above room temperature. Thus, the overall in uence of pressure on S (T) of $C \in Ru_2 Ge_2$ ts rather well the behaviour sketched in R ef. [11].

The e ect of magnetic ordering in S (T) is obvious as $C \in R u_2 G \in C$ is compared with the non-magnetic LaR $u_2 G \in C$ (inset to Fig. 4). LaRu₂Ge₂ has a rather small S (3:5 V/K at 300 K) which decreases alm ost linearly in magnitude with decreasing temperature and reaches 0 at T 10 K [31, 32]. Thus, the low-tem perature S anom alies in S (T) of C eR u₂G e₂ at am bient pressure are caused by the occurrence of magnetic order. This im plies that S (T) of C eR u_2 G e_2 above T_N can be regarded as the superposition of the pressure independent linear-in tem perature electron-phonon term represented by LaR u_2 G e_2 and the incipient contribution characteristic of several HF compounds. That contribution has a negative peak centred at 80 K (ascribed to spin interactions [11]) and a positive peak above room tem perature (caused by the interplay of K ondo and crystal-eld e ects). At am bi-



FIG.4: Therm oelectric power S(T) of $C \in R u_2 G e_2$ above the critical pressure. S(T) is dominated by a high-tem perature m axim um. The inset show s the am bient pressure S(T) data of $C \in R u_2 G e_2$ [17] and its non-m agnetic counterpart LaR $u_2 G e_2$.

ent pressure, the absolute value of S is small (as for e.g. $C \in Au_2Si_2$ [33]) because the compound is far below the critical pressure.

IV. D ISC U SSIO N

Figure 5 shows a revised and extended (T;p) phase diagram of $C \in Ru_2G \in c_2$ based on the present S(T) and

(T) data as well as (T) and calorim etric experiments performed on samples of the same batch [16, 17, 18]. The di erent m agnetic phases in C eR u2 G e2 are assum ed to be the same as those found in the solid-solution CeRu₂ (Si_{4 x}Ge_x)₂ for 0 1 [34, 35]. For deх tails about the magnetic structures the reader is referred to Ref. [30] and references therein. Pressure on CeRu₂Ge₂ or replacing Ge by Si in CeRu₂ (Si_{1 x}Ge_x)₂ are equivalent, since the unit-cell volum e seems to be the crucial parameter to change J. This was concluded from the common (T;V) phase diagram of both systems [17, 20]. Them ain observation of interest is that the longrange m agnetic order is suppressed above a critical pressure p_c and a HF behaviour equivalent to CeRu₂Si₂ at



FIG.5: (T;p) phase diagram of CeRu₂Ge₂ obtained from electrical resistivity (half open symbols) [16, 17], calorim etric (open symbols) [18], and the combined (T) and S(T) (bold symbols) measurements. At low pressure a param agnetic (PM) to antiferrom agnetic (AFM I) phase transition occurs at T_N and a subsequent transition into a ferrom agnetic phase (FM) takes place at T_C. The FM ground state is suppressed at 2.3 (2) GPa and a second antiferrom agnetically ordered phase (AFM II) occurs below T_L. The combination of alldata suggests that long-range magnetic order is suppressed at a critical pressure p_c = 7.8 GPa. T is the position of a maximum in (T) whereas T_S and T_K represent the centre of peaks in S (T). The half lled diam onds indicate T_K / 1= \overline{A} [17]. They are shifted by 1.4 GPa tow ards low er pressure (see text).

am bient pressure is expected. The present data show that the long-range magnetic order was suppressed between 5.7 GPa and 7 GPa. Therefore, we will assume $p_c = 6.4$ GPa as a rough estimate. U sing all p_c values determ ined on samples of the same batch [16, 17, 18] including this work, we estimate $p_c = 7.8$ GPa for C eRu₂Ge₂. Depending on the experimental method a slightly lower ($p_c = 6.9$ GPa [18]) or a higher value ($p_c = 8.7$ GPa) of p_c was reported in Ref. [16, 17]. This is partly due to the criterion used for the determination of p_c . As far as

(T) data of Ref. [17] are concerned, the pressures where the anomalies in the A (p) (at p = 7.3 GPa) or n (p) (at p = 8.2 GPa) dependences occur are a better choice of p_c than the T_N (p) ! 0 extrapolation (p = 8:7 G Pa). A and n were adjustable parameters in a tof (T) = $_0 + A T^n$ to the data below 1.5 K, with $_0$ the measured residual resistivity.

Knowing the (I;p) phase diagram one is tempted to label the features in S (T) (Fig. 3). It seem s that a discontinuity in the slope of S (T) can be used as de nition of T_N forp 2:1 G Pa, sim ilar to the case of C eC u₂G e₂ [10]. At p 5:7 GPa how ever, T_N yields no signature in S (T) as e.g. in the case of $C \in A_2$ ($T_N = 3:8 \times [3]$ at p = 0). From the (T) data recorded at 5.7 GPa it is inferred that $T_{\rm N}\,$ is located slightly below the maximum of the broad peak centred at 12 K. The signature of the FM transition is obscure. If it is related to the strong decrease of S(T) below about 7 K (for p 0:9 GPa) then the rather constant S (T) between 2 K and 5 K found at 2.1 GPa (inset to Fig. 3) would indicate that the ferrom agnetic order is already suppressed. The maximum at about 3 K in the 5.7 GPa data seems to be caused by $T_{
m L}$. The assignm ent of the rem aining, strongly pressure dependent pronounced maximum as T_K is then quite obvious for 5:7 GPa. It m ight be speculated whether the broad р feature below 2 K (for 3:4 GPa) is a signature of T_K or related to the magnetic order.

The interpretation of this pronounced low -tem perature feature as signature of the K ondo e ect is supported by the comparison of S (T) of $CeRu_2Ge_2$ at 7.0 GPa and $C \in R u_2 S i_2$ at am bient pressure [6] (F ig. 6). It is im portant to note that in both cases S (T) was measured perpendicular to the c-axis of the tetragonal crystal structure. The low-tem perature maximum in CeRu₂Si₂ occurs at 25 K close to the value of $T_{K} = 24 \text{ K}$ extracted from speci c heat m easurem ents using a single-im purity m odel [24]. Rem iniscent to this is the weak maximum in S(T) at 28 K for $CeRu_2Ge_2$ at 7.0 GPa. This agreement is not accidental since also the high-tem perature maximum occurs at the sam e tem perature T_S and has a sim ilar m agnitude as for CeRu₂Si₂. In S (T) of CeRu₂Si₂ it coincides with the temperature of the st excited crystal-eld level ($_1 = 220 \text{ K}$), deduced from a Schottky anomaly in the speci c heat 24]. Such a perfect agreem ent of calorim etric and transport data is fortuitous since it depends on T_K , the crystal- eld splitting, and the degeneracy of the crystal-eld levels \$6]. However, it applies also to $CeCu_6$ [37] and $CePd_2Si_2$ [11]. Thus, the peak in S(T) of $CeRu_2Ge_2$ at T_S can be ascribed to the interplay between incoherent K ondo scattering and crystal-elde ects. This comparison shows that the rst excited crystal-eld level in CeRu2Ge2 decreased from about 500 K [22, 23] to about 200 K for pressures in the vicinity of pc and explains why a high-tem perature maximum in (T) (Fig.2) was only seen in a certain pressure range above p_c. Furtherm ore, the resemblance of both S (T) curves con m s the assumption of p. 6:4 GPa.

The qualitative and quantitative agreement of both data sets can even be used to state that the occurrence of an in ection point in S (T) of C eRu₂G e₂ at about 50 K m ight im ply the change of regime as in $CeRu_2Si_2$ [6].



FIG. 6: Comparison of S(T) of CeRu₂Ge₂ at 7.0 GPa and CeRu₂Si₂ at am bient pressure [37]. Both curves reveal a pronounced high-tem perature maximum and a moderate positive contribution to S(T) at about 25 K. Inset: The low tem perature part of S(T) of CeRu₂Si₂ contains an additional positive peak below 1 K.

Slightly above this tem perature short-range AFM intersite correlations em erge in C eR u_2 Si₂ at am bient pressure [38, 39]. In addition a SR investigation [40] revealed m agnetic correlations below 1 K. These quasi-static correlations involve very small m agnetic m om ents of the order of 10³ _B. The origin of this weak static m agnetism well below T_K m ight be due to the formation of HF m agnetism involving the renormalised quasi-particles [40]. The presence of such correlations m ight be responsible for the positive contribution to S (T) below 1 K (inset to Fig. 6) and can be expected to occur also in C eR u_2 G e₂ below 1 K.

The very rapid increase of $T_{\rm K}~$ with pressure is corroborated by the reported pressure dependence of the A-coe cient [17], which was deduced from a t of (T) = $_0$ + AT 2 to the data for T < 0.5 K. Assuming that the relation A / 1= $T_{\rm K}^2$ holds, we calculated $T_{\rm K}$ (p) and added it to the phase diagram (Fig. 5). In order to do so, these values were normalised in such a way that at 7.0 GPa $T_{\rm K}$ = 24 K was in agreement with $T_{\rm K}$ deduced from the S (T) data. Furthermore, the calculated $T_{\rm K}$ (p) data had to be shifted towards lower pressure ($p_{\rm c}$ = 1:4 GPa)

to account for the di erent p. values. The norm alisation is in part arbitrary because the S (T) contribution gives only an estimation of $T_{\ensuremath{K}}$. But the pressure variations are reliable and noteworthy. Note here that one com pares the energy scale T_K with the ground state excitations, im plying that only one energy scale exists and that notably T_K is nite at p. The T_K (p) dependence revealed the interesting nding that two pressure ranges exist with quite di erent slopes in the T_K vs. p plot. Comparable $@T_K = @p$ values are observed for pressures ranging from about 6.5 GPa to 7 GPa and above 8.5 GPa. A much larger slope is found at interm ediate pressures (7 GPa p 8:5 GPa), i.e. around p_c. The transition from a large to a sm all $QT_K = Qp$ value is rem in iscent to the change in the slope of $T_K \ \text{vs.} \, p \ \text{observed}$ in $C \, \text{eR} \, u_2 \, \text{Si}_2$ at about 1 G P a [41]. A weaker than exponential variation of T_K (p) due to intersite interaction, proposed in Ref. [42], is not seen. If such a trend exist it seems to be restricted to pressures well below p_{c} .

The extrapolation of $T_{\rm K}$ (p) seems to merge with $T_{\rm S}$ (p) at pressures above 11 GPa, indicating the entrance into the IV regime (Fig. 5). Here, $k_{\rm B}\,T_{\rm K}\,$ exceeds the crystaled splitting and the entire six-fold degeneracy of the Ce-4f multiplet is recovered. So far, similar pressure dependences of two maxima in (T) were found for CeCu_2Ge_2 [28], CePd_2Si_2 [43], CePd_2Ge_2 [27], and CeCu_5Au [29]. The pressure $p_{\rm V}\,$ 11 GPa for CeRu_2Ge_2, where $T_{\rm K}\,$ $T_{\rm S}$, might de ne the region where the valence of the Ce-ion starts to increase.

B and structure calculations [44] supported e. g. by de Haas-van Alphen (dHvA) measurements [45] have shown that the $4f^{\dagger}$ Ce electron does not participate to the Ferm i surface of CeRu₂Ge₂ as it is the case for CeRu₂Si₂ [46, 47, 48]. The comparison between dHvA frequency-branches of CeRu₂Ge₂ and the theoreticalbranches of LaRu₂Ge₂ in plies that the 4f electron in CeRu₂Ge₂ is fully localised in the ground state [44]. O ne of the original motivation of the present transport investigation was to follow the promotion of this 4f electron. How ever, the data do not show any distinct pressure or a pressure range where the $4f^{\dagger}$ electron becomes delocalized in CeRu₂Ge₂. Neither the residual resistivity [28] nor a plot of S=T at 1.5 K reveals a distinct feature related to the promotion of the $4f^{\dagger}$ electron. S=T at 1.5

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K has a marked maximum around 6 GPa but it seems to be correlated to T_L . It is also noteworthy that close to p_c , S=T vs T is without any anomaly and does not con m the predictions of R ef. [9]. Thus, the question can be asked whether the nature of the pressure-induced quantum discontinuity is of second order or if it really exists in C eR u_2 G e_2 .

V. CONCLUSION

The in uence of pressure on the tem perature dependence of the therm oelectric power S (T) of C eR u_2 G e_2 was m easured up to 16 GPa. The various m agnetic phase transitions below 10 K yield a complex S (T) behaviour. A large positive peak in S (T) centered at T_S just below room temperature starts to develop at pressures above 3 G Pa. It is ascribed to the interplay between incoherent Kondo scattering and crystal-eld e ects. A pressureinduced low-tem perature maximum in S (T) at T_K develops in the range 5.7 GPa p 8 GPa. It is interpreted as a signature of the K ondo e ect, sigce its position shows a sim ilar pressure dependence as 1= A (p). This im plies that only one energy scale seems to exists in $C \mathrel{\mbox{eR}} u_2 \mathrel{\mbox{G}} e_2$. A revised (T;p) phase diagram, based on transport and calorim etric investigations on sam ples of the sam e batch, suggests that in $C \in Ru_2G \in 2$ long-range m agnetic order is suppressed at a critical pressure $p_c = 7.8$ GPa. Well above p_c , the T_K (p) and T_S (p) dependences m erge at a pressure p_v 11 GPa, de ning a pressure range where the Ce-valence starts to increase.

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